Part Number	Customer

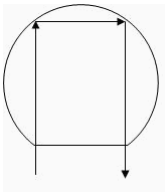
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none or semi standard	
	5.0	Secondary Flat Length	None / 18.0mm +/- 2.0mm	Wafer Vendor
	6.0	Overall Thickness	634.00 +/- 12.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<150.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<150.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	14.0	Handle Thickness	550.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	<1 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide and scribe	Guaranteed by Process
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	20,000.00 +/- 2,000.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	24.0	Nominal Thickness	40.00 +/- 0.50 µm	FTIR, 100% 9-Pt (note3)
	25.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	26.0	Device Doping Type	P	Wafer Vendor
	27.0	Device Dopant	Boron	Wafer Vendor
	28.0	Device Resistivity	<1 Ohmcm	Wafer Vendor
BuriedOxide2	29.0	Oxide 2 Type	Thermal	
	30.0	Oxide 2 Thickness	20,000.00 +/- 2,000.00 A	Nanospec centre point measurement, 4%
DeviceSilicon2	31.0	Device 2 Growth Method	CZ	Wafer Vendor
	32.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	33.0	Device 2 Nominal Thickness	40.00 +/- 1.00 um	ADE Single Point, 100%
	34.0	Distance to Device 2 edge from wafer edge	< = 3mm	Guaranteed by Process

Part Number	Customer

Category		Parameter	Specification	Measurement Method
DeviceSilicon2	35.0	Device 2 DopingType	P	Wafer Vendor
	36.0	Device 2 Dopant	Boron	Wafer Vendor
	37.0	Device 2 Resistivity	<1 Ohmcm	Wafer Vendor
DeviceSilicon	38.0	Voids	none	Wafer Vendor
	39.0	Scratches	0	Bright Light, 100% (note 2)
	40.0	Haze	none	Bright Light, 100% (note 2)

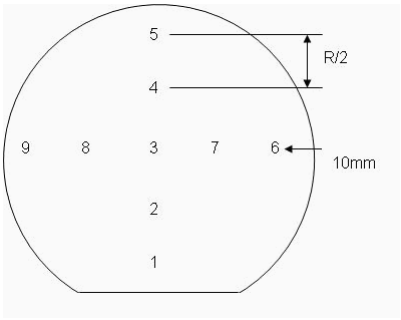
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information